

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
40V	6.5mΩ @ V _{GS} = 10V	85A
	9.8mΩ @ V _{GS} = 4.5V	70A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Thermally Efficient Package – Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile – Ideal for Thin Applications
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **An automotive-compliant part is available under separate datasheet ([DMTH4007LPSWQ](#))**

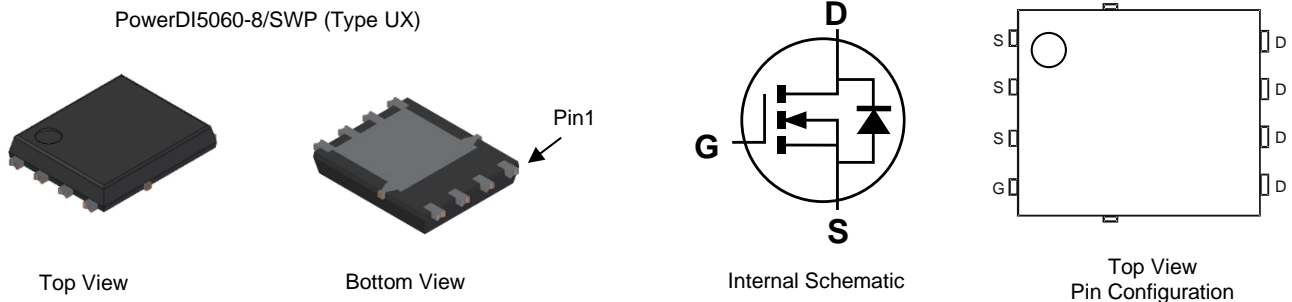
Description and Applications

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance.

- Notebook battery power managements
- DC-DC converters
- Load switches

Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.097 grams (Approximate)

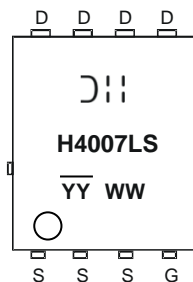


Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMTH4007LPSW-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



- = Manufacturer's Code Marking
- H4007LS = Product Type Marking Code
- YYWW = Date Code Marking
- YY = Last Two Digits of Year (ex: 24 = 2024)
- WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	40	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	T _A = +25°C	I _D	15	A
	T _A = +100°C		11	
Continuous Drain Current, V _{GS} = 10V (Note 6)	Steady State	I _D	85	A
			T _C = +100°C	
Maximum Continuous Body Diode Forward Current (Note 6)		I _S	85	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	340	A
Avalanche Current, L = 0.1mH		I _{AS}	20	A
Avalanche Energy, L = 0.1mH		E _{AS}	20	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	55	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	P _D	83.3	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	1.8	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 32V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	5.4	6.5	mΩ	V _{GS} = 10V, I _D = 20A
		—	8.4	9.8		V _{GS} = 4.5V, I _D = 20A
Diode Forward Voltage	V _{SD}	—	—	1.2	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	1,895	—	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	485	—		
Reverse Transfer Capacitance	C _{rss}	—	20.9	—		
Gate Resistance	R _g	—	0.62	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	12.4	—	nC	V _{DS} = 30V, I _D = 20A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	29.1	—		
Gate-Source Charge	Q _{gs}	—	5.9	—		
Gate-Drain Charge	Q _{gd}	—	3.5	—		
Turn-On Delay Time	t _{D(ON)}	—	5.4	—	ns	V _{DD} = 30V, V _{GS} = 10V, I _D = 20A, R _G = 3Ω
Turn-On Rise Time	t _R	—	4.5	—		
Turn-Off Delay Time	t _{D(OFF)}	—	16.2	—		
Turn-Off Fall Time	t _F	—	3.5	—		
Body Diode Reverse Recovery Time	t _{RR}	—	30.6	—	ns	I _F = 20A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	28.1	—	nC	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

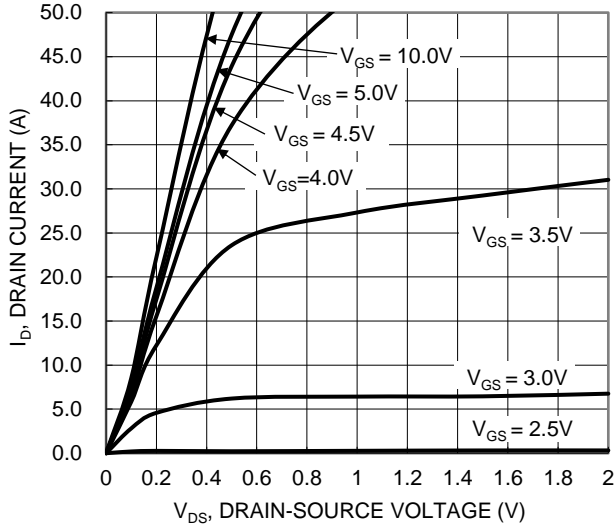


Figure 1. Typical Output Characteristic

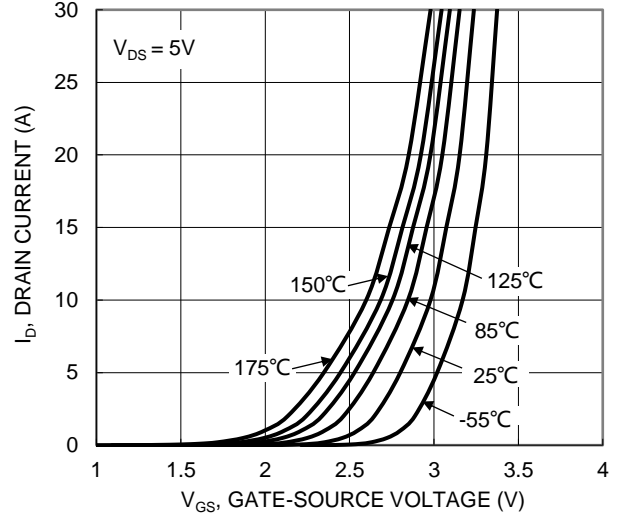


Figure 2. Typical Transfer Characteristic

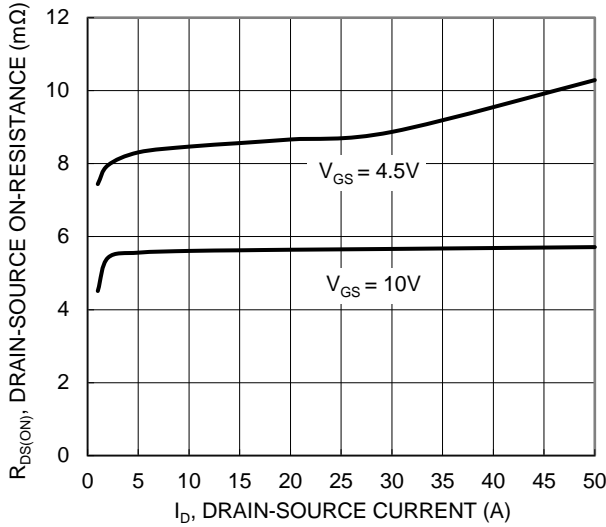


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

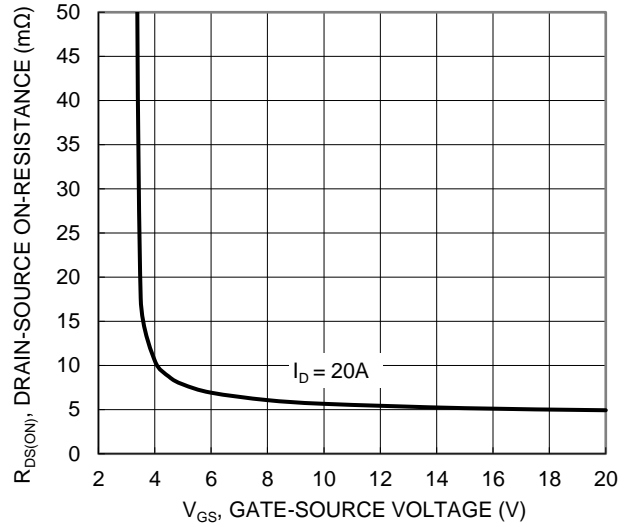


Figure 4. Typical Transfer Characteristic

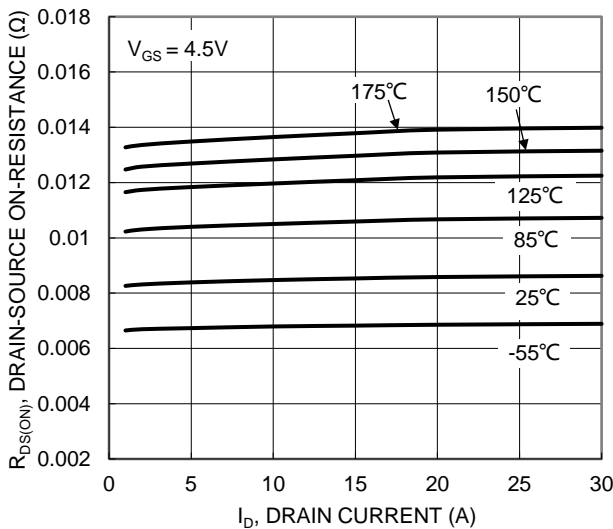


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

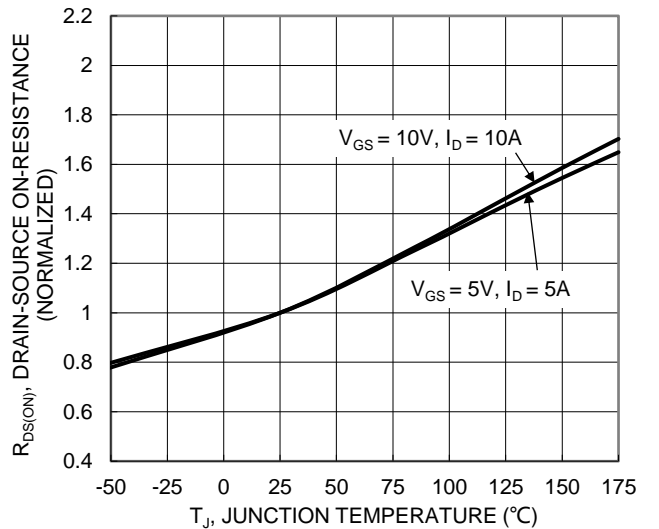


Figure 6. On-Resistance Variation with Temperature

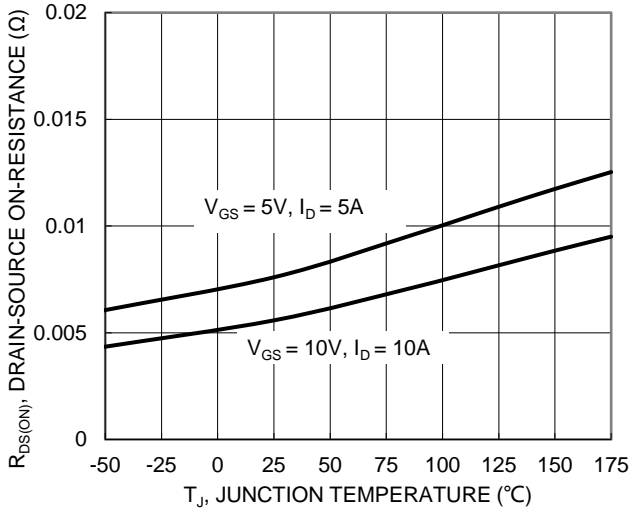


Figure 7. On-Resistance Variation with Temperature

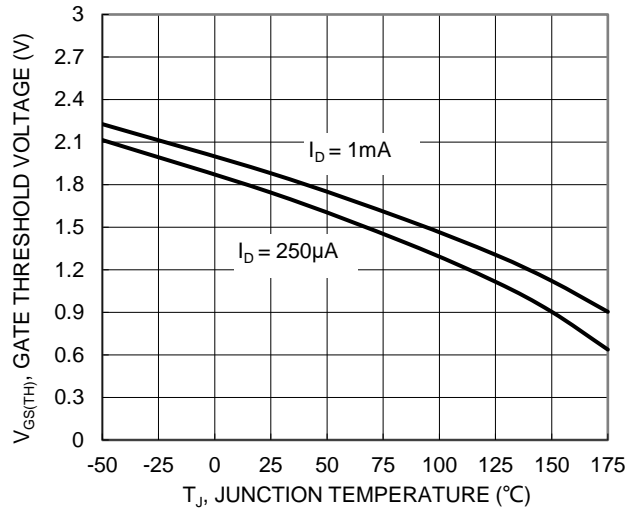


Figure 8. Gate Threshold Variation vs. Junction Temperature

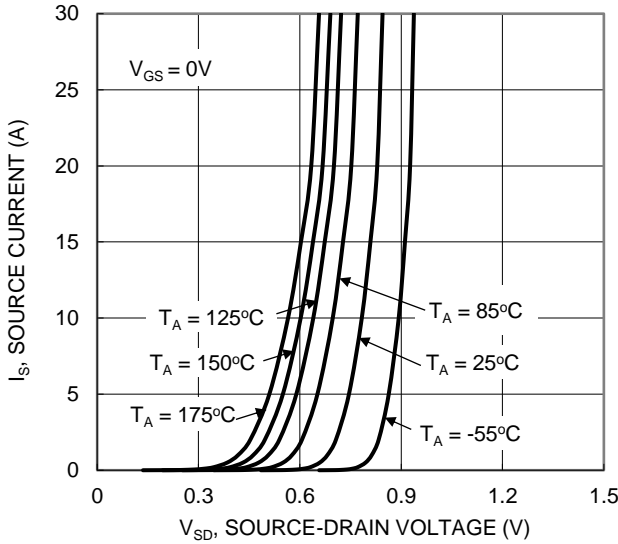


Figure 9. Diode Forward Voltage vs. Current

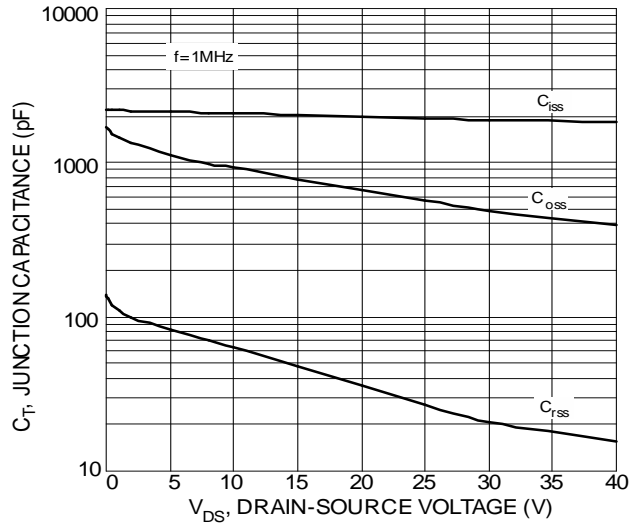


Figure 10. Typical Junction Capacitance

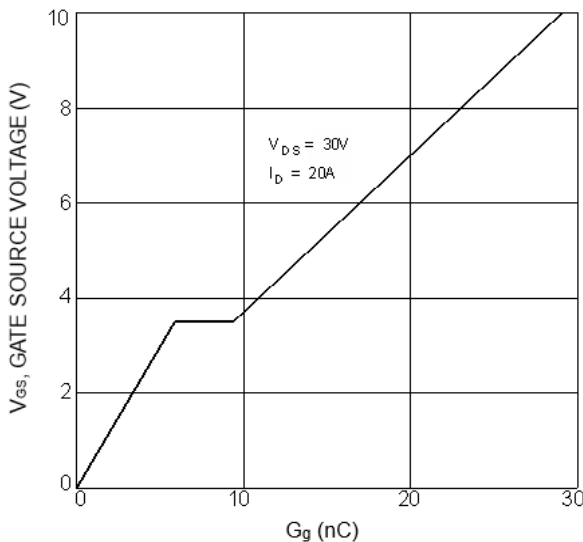


Figure 11. Gate Charge

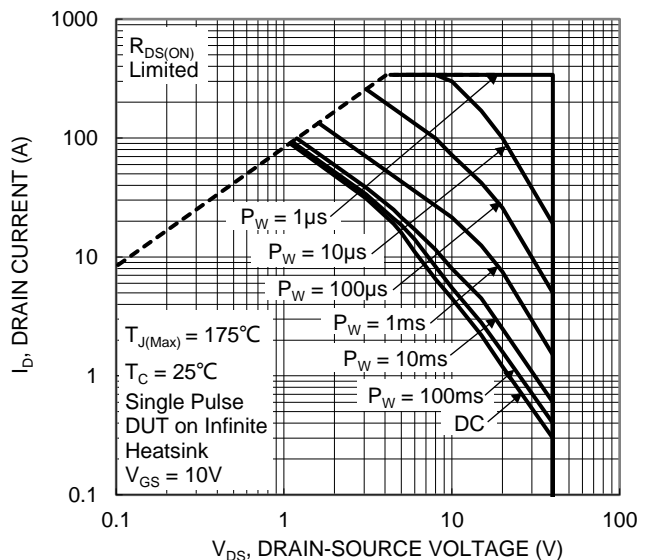
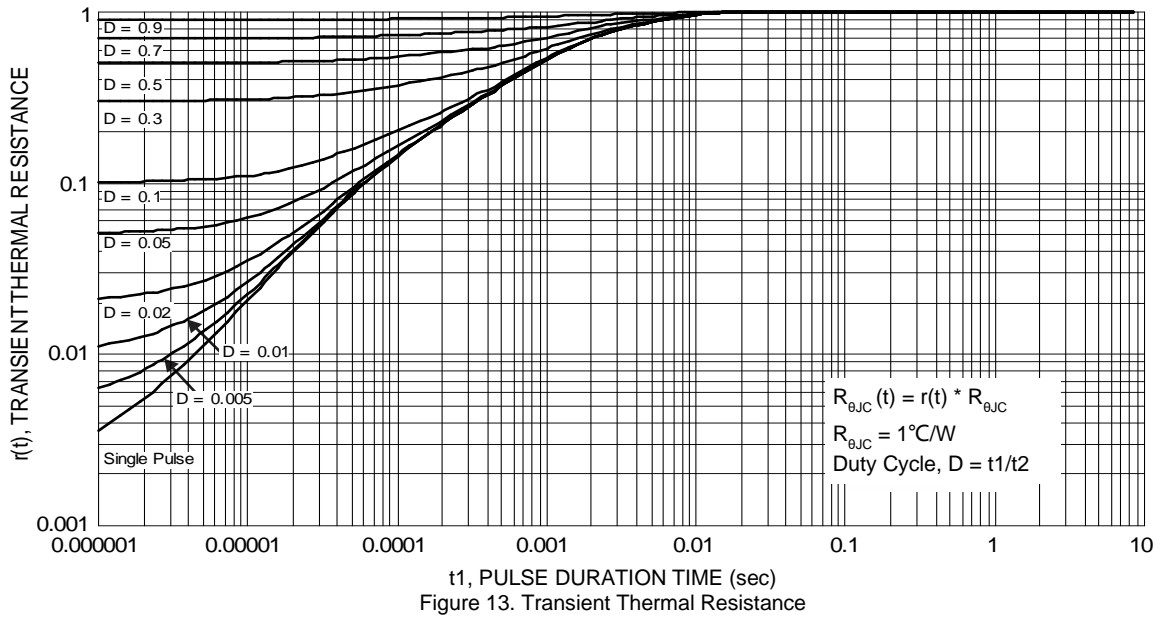


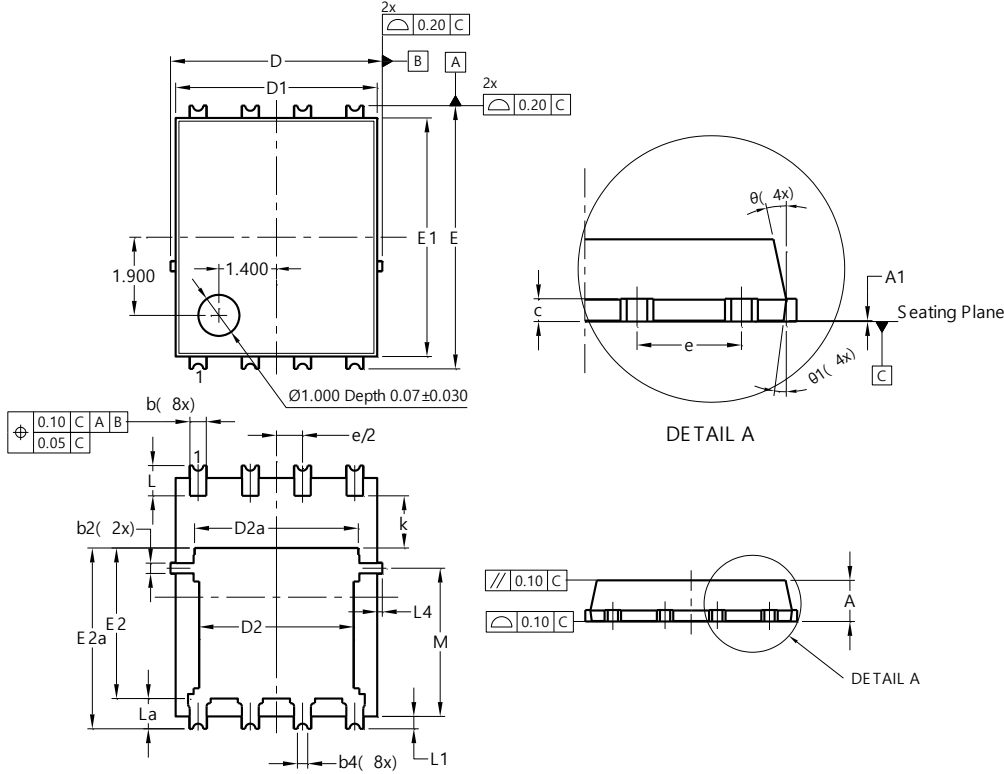
Figure 12. SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8/SWP (Type UX)

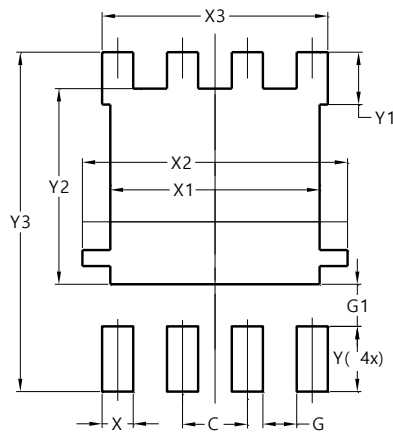


PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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